

N-channel 80 V, 9.9 mΩ standard level MOSFET in LFPAK56 8 May 2013 Product data sheet

1. General description

Standard level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	80	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	89	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	195	W
Static charact	eristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	7.3	9.9	mΩ
Dynamic char	acteristics			1		
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 25 A; V _{DS} = 64 V; Fig. 13; Fig. 14	-	14.4	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
BUK7Y9R9-80E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7Y9R9-80E	79E980

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

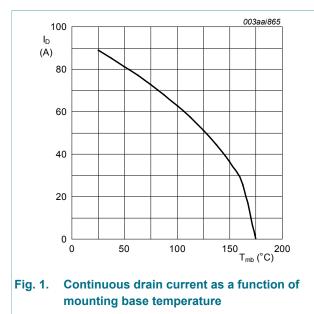
Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	80	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	80	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC	-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	89	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	63	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4	-	354	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	195	W
T _{stg}	storage temperature		-55	175	°C

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Symbol	Parameter	Conditions		Min	Мах	Unit
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C		-	89	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	354	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ I_D = 89 \text{ A}; V_{sup} \le 80 \text{ V}; \text{ R}_{GS} = 50 \Omega; V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ unclamped}; Fig. 3 $	[1][2]	-	106	mJ

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 $^\circ\text{C}.$

[2] Refer to application note AN10273 for further information.



 $V_{GS} \ge 10V$

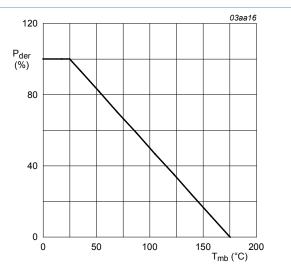
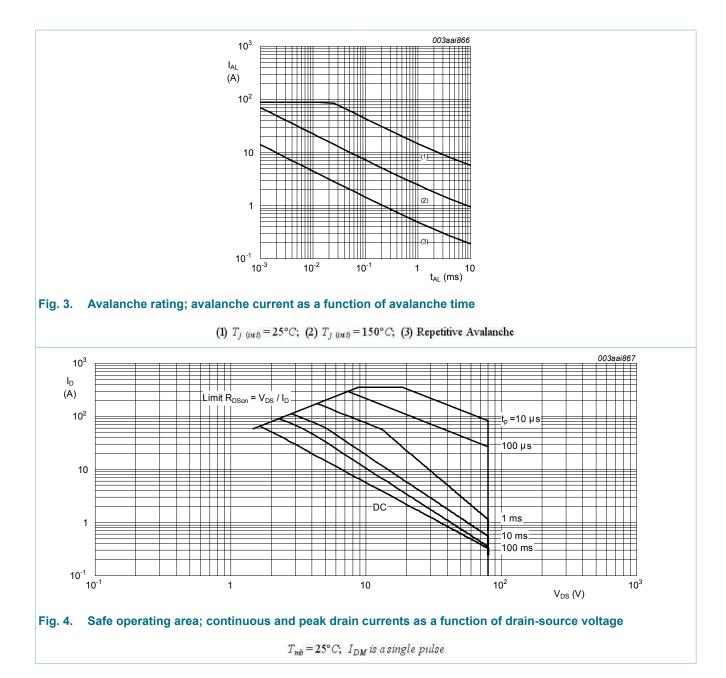


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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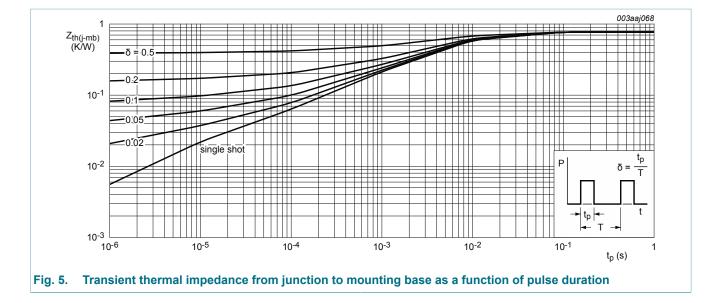
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9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.77	K/W

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · ·	1			
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	80	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	72	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	4.5	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 9	1	-	-	V
I _{DSS} drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.13	10	μA	
		V_{DS} = 80 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS} gate leakage current	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	24.9	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	7.3	9.9	mΩ
Dynamic ch	naracteristics	· · · · · ·	1			
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 64 V; V_{GS} = 10 V;	-	51.6	-	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	14.1	-	nC
Q _{GD}	gate-drain charge	1	-	14.4	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;		-	3200	4266	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	303	364	pF
C _{rss}	reverse transfer capacitance			-	165	226	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 60 \text{ V}; \text{ R}_{L} = 2.4 \Omega; \text{ V}_{GS} = 10 \text{ V};$ $\text{R}_{G(ext)} = 5 \Omega$		-	15	-	ns
t _r	rise time			-	23	-	ns
t _{d(off)}	turn-off delay time			-	34	-	ns
t _f	fall time			-	21	-	ns
Source-drai	n diode	1	I				
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>		-	0.83	1.2	V
t _{rr}	reverse recovery time	I_{S} = 20 A; dI_{S}/dt = -100 A/µs; V_{GS} = 0 V;		-	35	-	ns
Q _r	recovered charge	V _{DS} = 25 V		-	52	-	nC

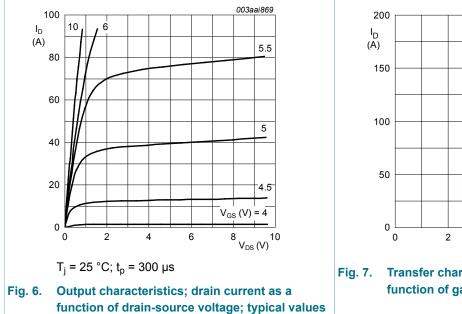
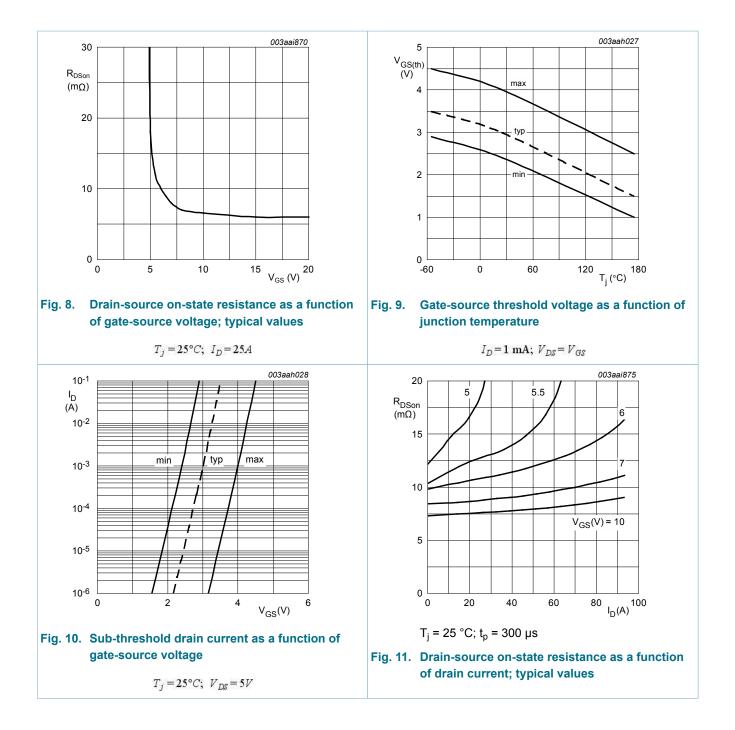


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

 $V_{DS} = 10V$

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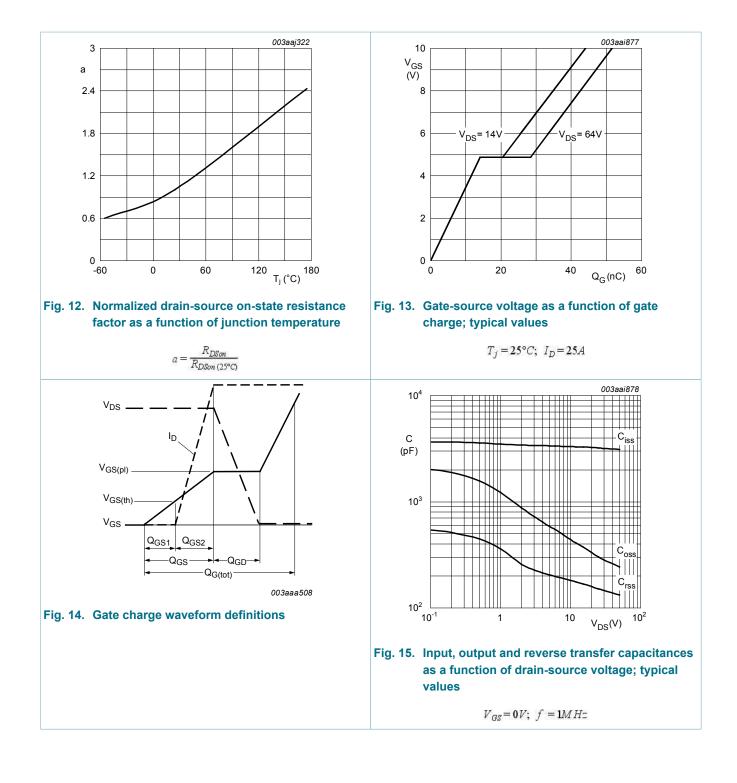
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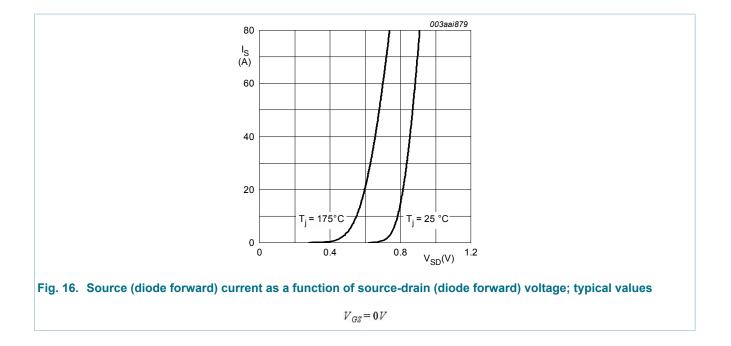
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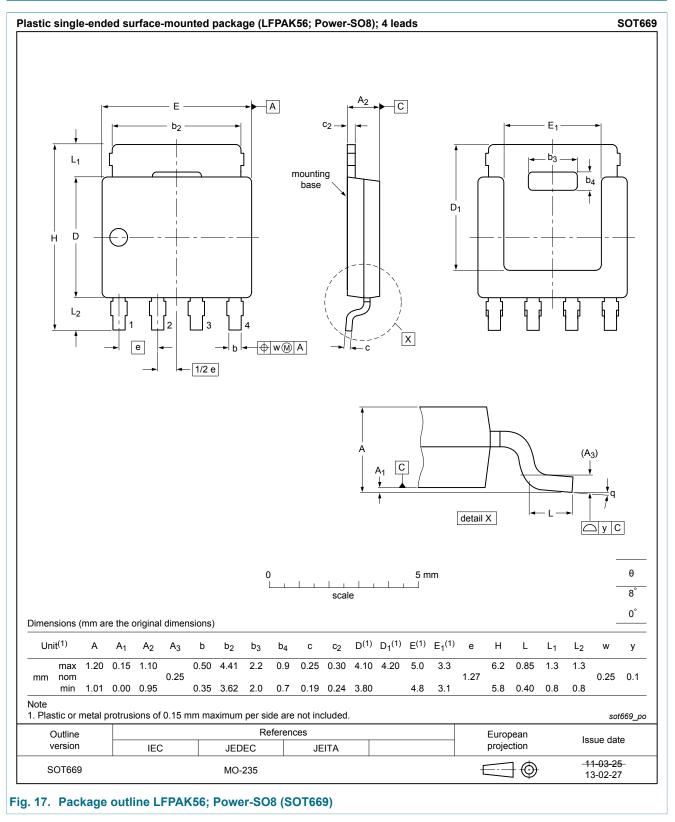
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11. Package outline



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12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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